

f Education

and Research

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PERFORMANCE OF PLANAR PIXEL MODULES FOR THE PHASE-2 UPGRADE OF THE CMS INNER TRACKER

<u>CMS Inner Tracker Upgrade for the High-Luminosity LHC</u>

The Inner Tracker of the Compact Muon Solenoid (CMS) experiment will be entirely upgraded for the High-Luminosity Phase of the Large Hadron Collider (HL-LHC)^[1].

Highlights

Luminosity: **7.5 x 10³⁴ cm⁻² s⁻¹**

Integrated luminosity: **3000 – 4000 fb**⁻¹

Pile-up: <µ> = **200**

 ϕ_{max} planar modules = 1 × 10¹⁶ n_{eq} cm⁻²

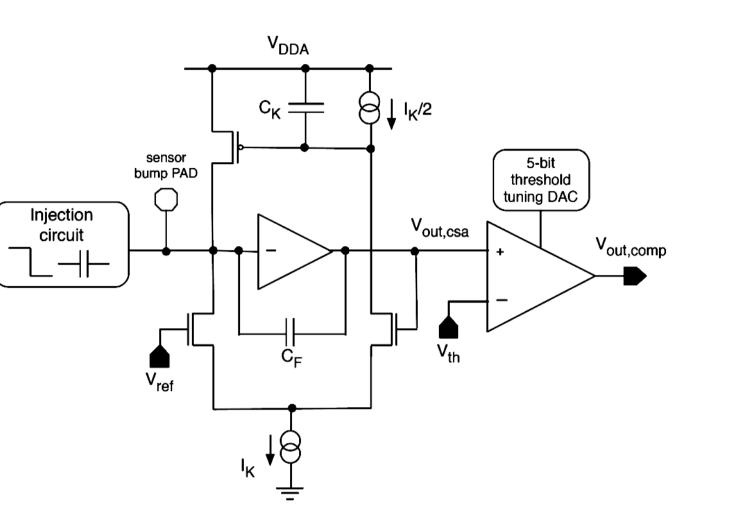
New pixel detectors for the CMS Inner Tracker

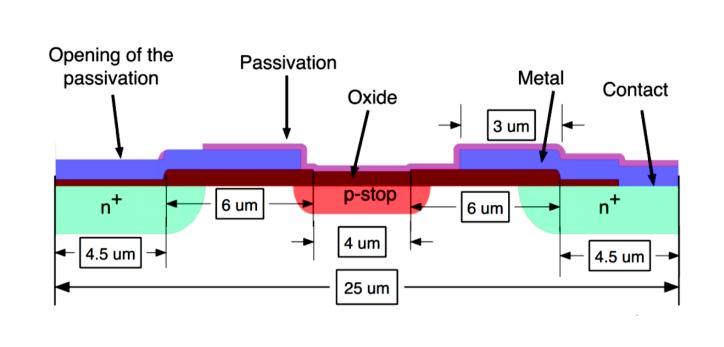
Pixel detectors of the Inner Tracker will feature a new **readout chip** (RD53C_CMS) and **sensor design**

RD53B_CMS readout chips^[2]

Implemented in 65 nm CMOS radiation-hard technology:

- > 432 x 336 pixels with 50 x 50 μ m² pitch
- Analog Front-End:
- Single stage with Krummenacher feedback





Planar sensors

- Low power comparator
- > 4 bit **counter** for charge digitization
- > 5 bit in-pixel DAC for **threshold tuning**



Pixels tuned to a **common threshold** to zero-suppress noise hits:

- Hit detection changes as function of time within the bunch crossing
- Feature of the readout's architecture
- Impact on the measured crosstalk (XT)

Crosstalk studies

Must remain <10% for all geometrical configurations:

- Coupled pixels (1-2) with highest inter-pixel capacitance (14 fF)
- Uncoupled pixels (1-3) with second highest (6.5 fF)
- > Avoid biasing of **reconstructed hit position**

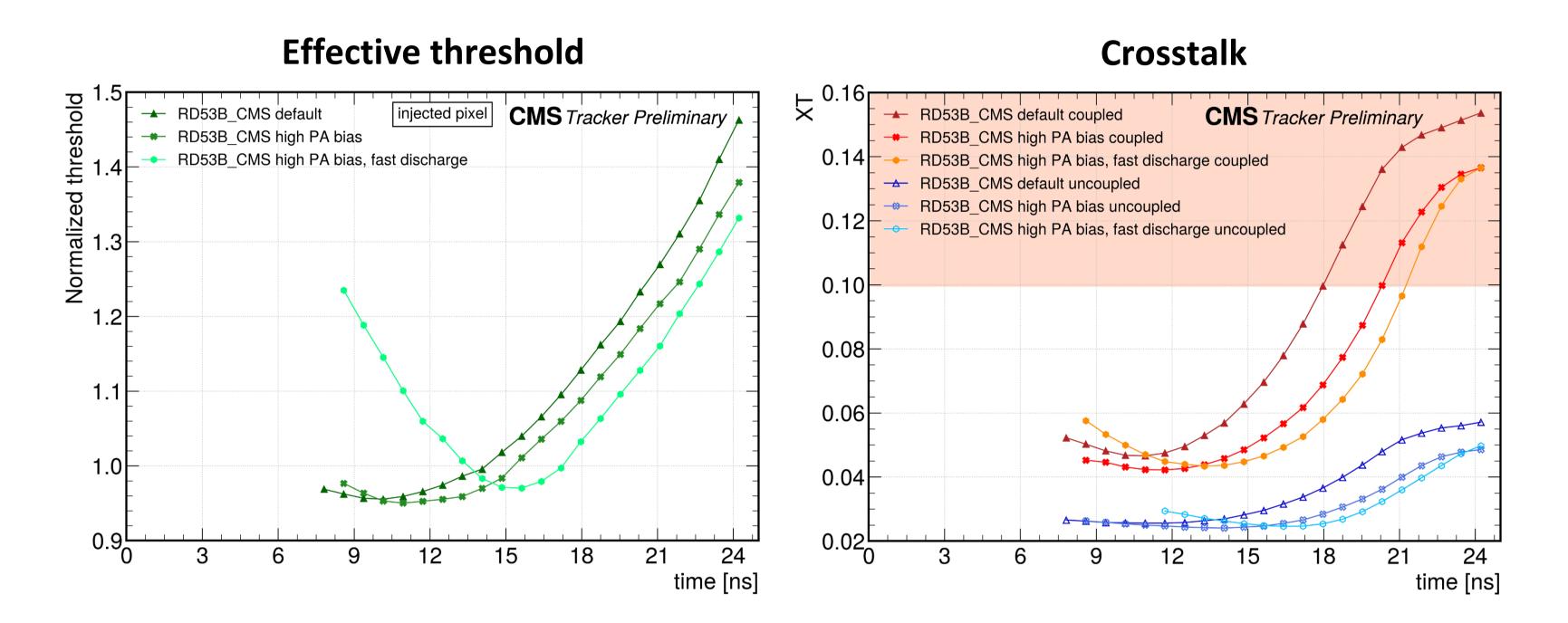
Phasing of clock in final experiment will target highest efficiency:

 \blacktriangleright Lowest threshold \rightarrow minimum of threshold near crosstalk minimum

n⁺-in-p Hamamatsu Photonics (HPK)

 \blacktriangleright Pitches of **25 x 100 \mum²** and active thickness of **150 \mum**

> **Bitten** design: cutout in the neighboring pixel



XT ~5% close to the threshold's minimum

<u>Test beam measurements</u>

Samples measured at DESY II Test Beam facility with **5.2 GeV e⁻/e⁺ beam**. Modules **irradiated with 24 GeV/c protons** at Proton Irradiation Facility:

- Non-uniform fluence across columns
- > Ranges from $\phi_{eq} = 0.5 \times 10^{16} \text{ cm}^{-2}$ to $\phi_{eq} = 1.0 \times 10^{16} \text{ cm}^{-2}$

Individual sections with different average fluences have been studied.

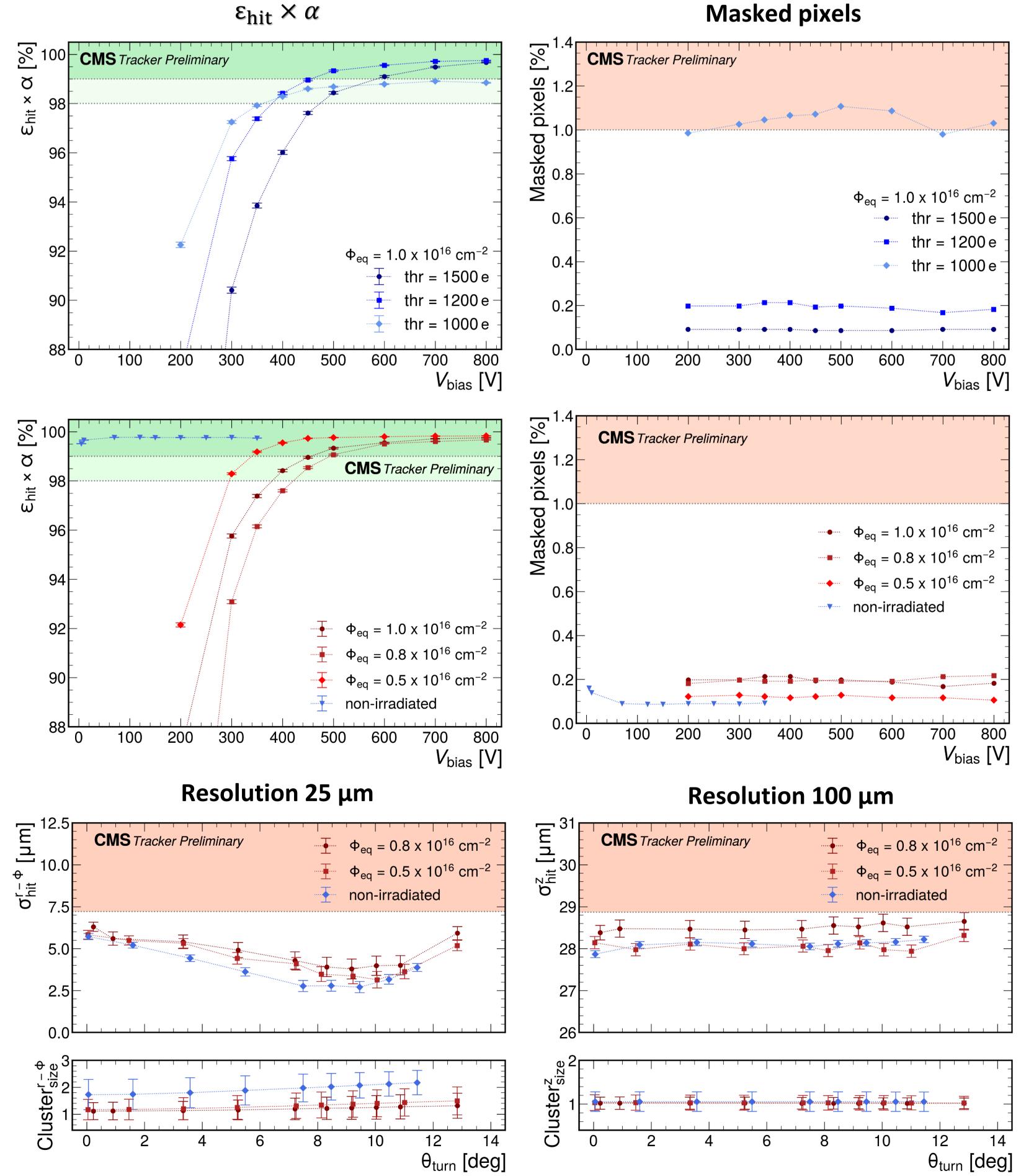
Observables
$$\varepsilon_{\text{hit}} = \frac{N_{\text{tracks}}^{\text{DUT}}}{N_{\text{tracks}}^{\text{total}}}$$
 $\alpha = 1 - \frac{N_{\text{masked}}^{\text{pxl}}}{N_{\text{total}}^{\text{pxl}}}$ $\sigma_{\text{hit}} = \sqrt{\sigma_{\text{res}}^2 - \sigma_{\text{tel}}^2}$

Main module requirements:

- > Number of masked pixels <1% (noise occupancy threshold < 10⁻⁴)
- > Average noise occupancy of unmasked pixels <10⁻⁶
- > At vertical incidence, for irradiated modules:

$$\phi_{\text{ref}} = 5 \times 10^{15} \, n_{\text{eq}} \text{cm}^{-2} \begin{cases} \Phi_{\text{eq}} < \Phi_{\text{ref}} & \varepsilon_{\text{hit}} \times \alpha > 99\% & V_{\text{bias}} \le 600 \, \text{V} \\ \Phi_{\text{eq}} > \Phi_{\text{ref}} & \varepsilon_{\text{hit}} \times \alpha > 98\% & V_{\text{bias}} \le 800 \, \text{V} \end{cases}$$

Studies on $\phi_{eq} = 1.0 \times 10^{16} \text{ cm}^{-2}$ for different **thresholds**:



- \succ Meet requirement for $\varepsilon_{hit} \times \alpha$
- > Noisy pixels above requirement for threshold = $1000 e^{-1}$

Threshold \geq 1200 e⁻ to fulful $\varepsilon_{hit} \times \alpha$ and noise requirements

- $\sigma_{
 m hit}$ better than binary limit before irradiation:
- Charge sharing

Aim after irradiation:

- > $\sigma_{hit}^{r-\phi} < 7.2 \, \mu m$ in r- ϕ (25 μm pixel pitch)
- > σ_{hit}^{z} < 28.9 μm in z (100 μm pixel pitch) direction

Planar sensors equipped with RD53B_CMS chips meet all requirements